

# EECS 42 Introduction Digital Electronics

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**2<sup>nd</sup> Midterm 11/6 See Coverage Sheet**

### Lecture # 19 Logic Transients

Handout of Wed Lecture.

**A) Quiz**

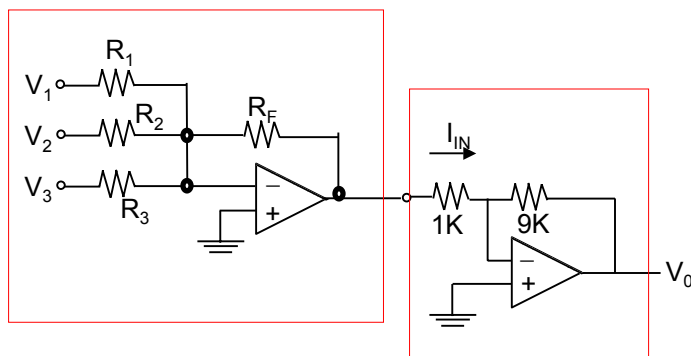
**B) Worst Case CMOS Delay**

**C) Delay in CMOS Cascade**

**<http://inst.EECS.Berkeley.EDU/~ee42/>**

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### CASCADE OP-AMP CIRCUITS



How do you get started on finding  $V_0$ ?

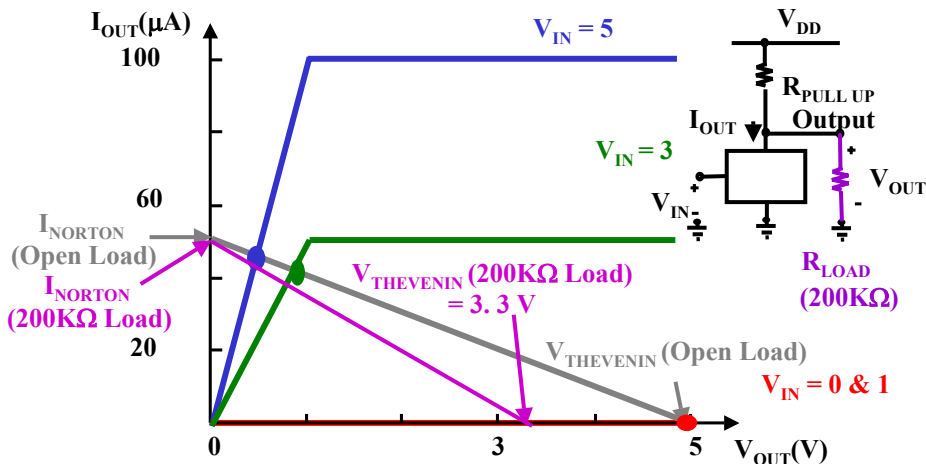
**Hint: Identify Stages**

**Hint:  $I_{IN}$  does not affect  $V_{O1}$**

See the further examples of op-amp circuits in the reader

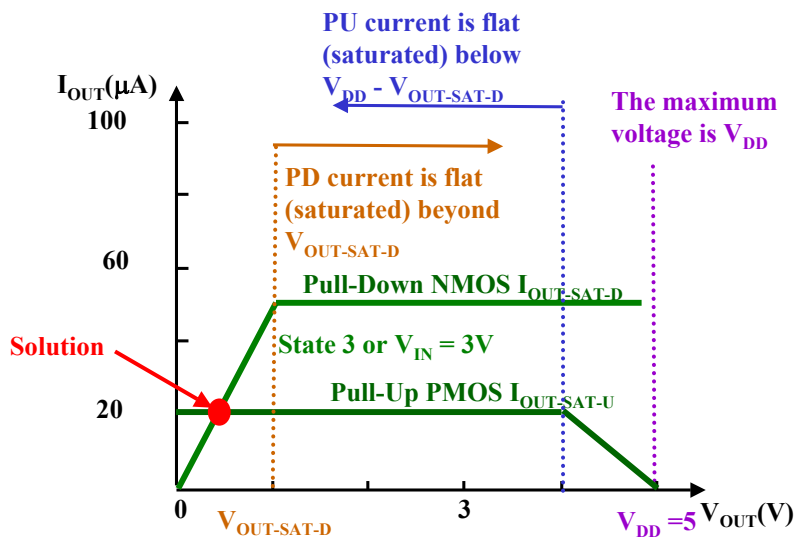
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# Composite Current Plot for the 42S\_NMOS Circuit with 200kΩ Load to Ground



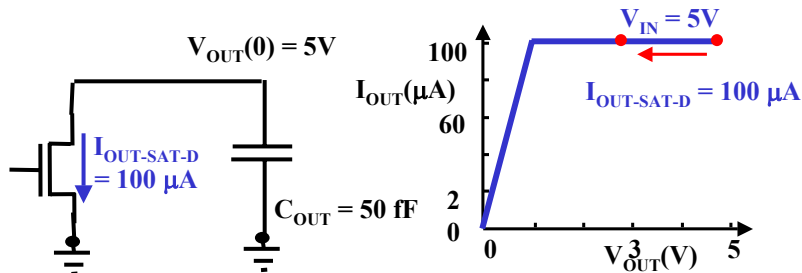
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# Composite $I_{OUT}$ vs. $V_{OUT}$ for CMOS



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## Output Propagation Delay High to Low (Cont.)



When  $V_{OUT} > V_{OUT-SAT-D}$  the available current is  $I_{OUT-SAT-D}$

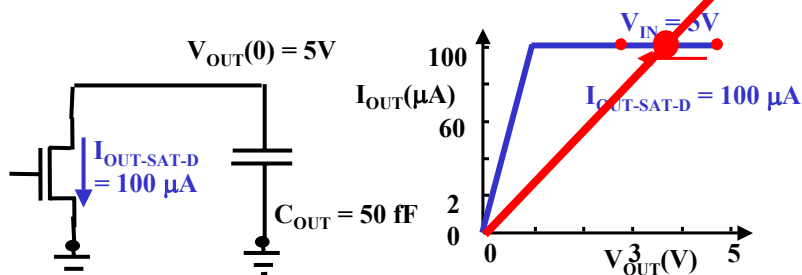
For this circuit when  $V_{OUT} > V_{OUT-SAT-D}$  the available current is constant at  $I_{OUT-SAT-D}$  and the capacitor discharges.

The **propagation delay** is thus

$$\Delta t = \frac{C_{OUT} \Delta V}{I_{OUT-SAT-D}} = \frac{C_{OUT} V_{DD}}{2 I_{OUT-SAT-D}} = \frac{50 \text{ fF} \cdot 2.5V}{100 \mu\text{A}} = 1.25 \text{ ns}$$

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## $R_D = \frac{3}{4} V_{DD} / I_{SAT}$ has a Physical Interpretation



$\frac{3}{4} V_{DD}$  is the average value of  $V_{OUT}$

Approximate the NMOS device curve by a straight line from  $(0,0)$  to  $(I_{OUT-SAT-D}, \frac{3}{4} V_{DD})$ .

Interpret the straight line as a resistor with

$$\text{slope} = 1/R = \frac{3}{4} V_{DD} / I_{SAT}$$

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## Switched Equivalent Resistance Values

The resistor values depend on the properties of silicon, geometrical layout, design style and technology node.

n-type silicon has a carrier mobility that is 2 to 3 times higher than p-type.

The resistance is inversely proportion to the gate width/length in the geometrical layout.

Design styles may restrict all NMOS and PMOS to be of a predetermined fixed size.

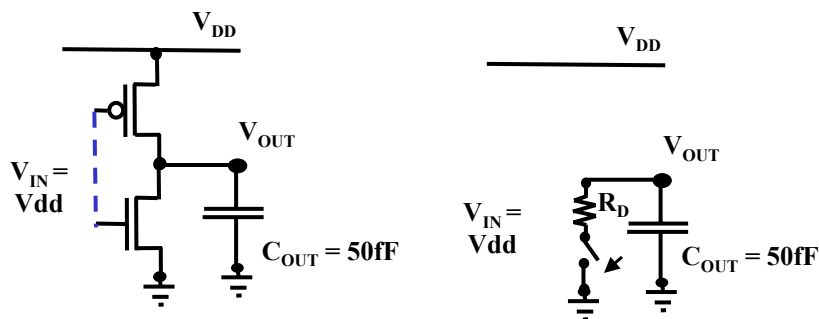
The current per unit width of the gate increases nearly inversely with the linewidth.

**For convenience in EE 42 we assume**  
 $R_D = R_U = 10 \text{ k}\Omega$  for  $V_{DD} = 5\text{V}$  and  
 $R_D = R_U = 10 \text{ k}\Omega$  for  $V_{DD} = 5\text{V}$

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## Inverter Propagation Delay

Discharge (pull-down)



$$\Delta t = 0.69R_D C_{OUT} = 0.69(10\text{k}\Omega)(50\text{fF}) = 345 \text{ ps}$$

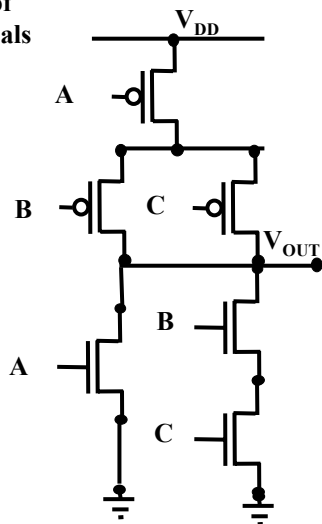
Discharge (pull-up)

$$\Delta t = 0.69R_U C_{OUT} = 0.69(10\text{k}\Omega)(50\text{fF}) = 345 \text{ ps}$$

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NMOS and PMOS use the same set of input signals

## CMOS Logic Gate



PMOS only in pull-up

PMOS conduct when input is low

PMOS do not conduct when  $A + (BC)$

NMOS only in pull-down

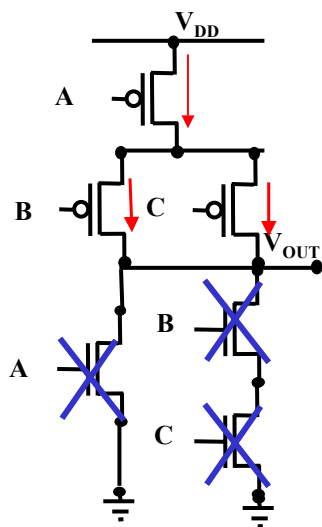
NMOS conduct when input is high.

NMOS conduct for  $A + (BC)$

Logic is Complementary and produces  $F = \overline{A + (BC)}$

## CMOS Logic Gate: Example Inputs

A = 0  
B = 0  
C = 0



PMOS all conduct

Output is High

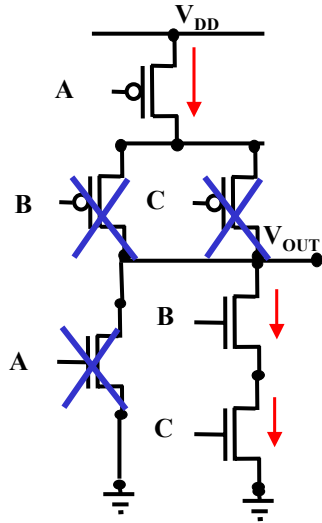
=  $V_{DD}$

NMOS do not conduct

Logic is Complementary and produces  $F = 1$

# CMOS Logic Gate: Example Inputs

A = 0  
B = 1  
C = 1



PMOS A conducts; B and C Open

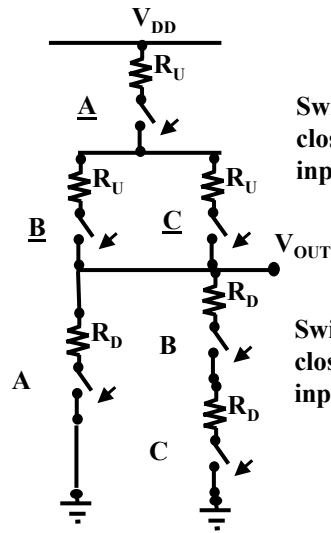
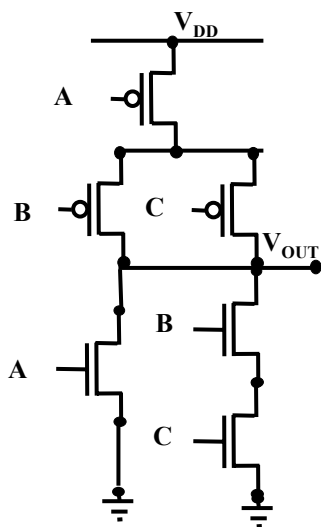
Output is High

**= 0**

NMOS B and C conduct; A open

Logic is Complementary and produces F = 0

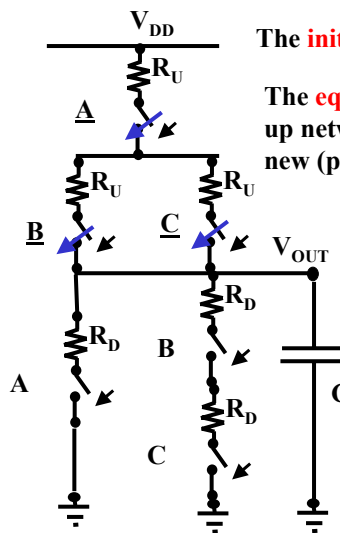
# Switched Equivalent Resistance Network



Switches close when input is low.

Switches close when input is high.

## Logic Gate Propagation Delay: Initial State



The **initial state** depends on the old (previous) inputs.

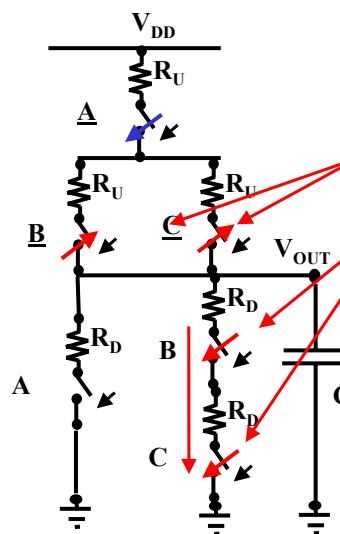
The **equivalent resistance** of the pull-down or pull-up network for the transient phase depends on the new (present) input state.

**Example:** A=0, B=0, C=0 for a long time.

These inputs provided a path to  $V_{DD}$  for a long time and the capacitor has precharged up to  $V_{DD} = 5V$ .

$C_{OUT} = 50 \text{ fF}$

## Logic Gate Propagation Delay: Transient



At  $t=0$ , B and C switch from low to high ( $V_{DD}$ ) and A remains low.

This breaks the path from  $V_{OUT}$  to  $V_{DD}$

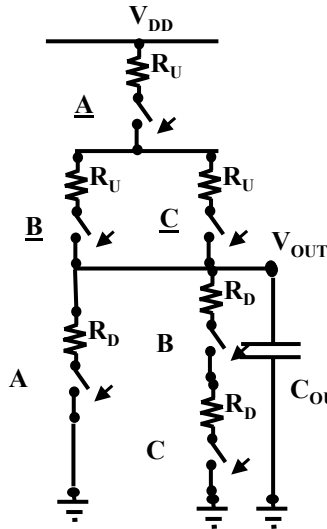
And opens a path from  $V_{OUT}$  to GND

$C_{OUT}$  discharges through the pull-down resistance of gates B and C in series.

$$\Delta t = 0.69(R_{DB} + R_{DC})C_{OUT} = 0.69(20k\Omega)(50fF) = 690 \text{ ps}$$

The propagation delay is **two times longer** than that for the inverter!

## Logic Gate: Worst Case Scenarios



What combination of previous and present logic inputs will make the Pull-Up the **fastest**?

**Fastest overall?**

What combination of previous and present logic inputs will make the Pull-Up the **slowest**?

**Slowest overall?**

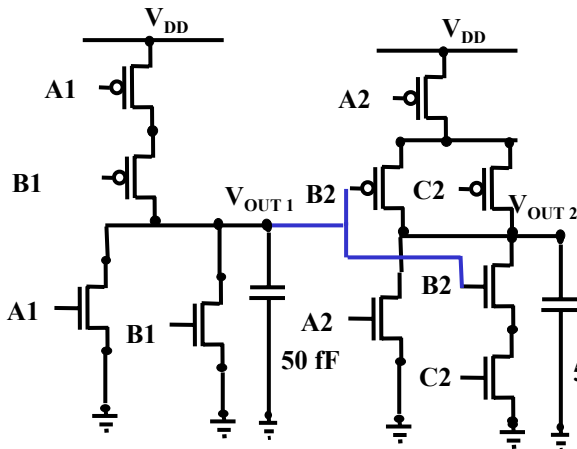
What combination of previous and present logic inputs will make the Pull-Down the **fastest**?

What combination of previous and present logic inputs will make the Pull-Down the **slowest**?

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## Logic Gate Cascade

To avoid large resistance due to many gates in series, logic functions with 4 or more inputs are usually made from cascading two or more 2-4 input blocks.



$B2 = V_{OUT1}$

The four independent input are A1, B1, A2 and C2.

A2 high discharges gate 2 without even waiting for the output of gate 1.

C2 high and A2 low makes gate 2 wait for Gate 1 output

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